

# ROHS V EARTH FRIENDLY

HMC373LP3 / 373LP3E

v03.0610

### GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz

### **Typical Applications**

The HMC373LP3 / HMC373LP3E is ideal for basestation receivers:

- GSM, GPRS & EDGE
- CDMA & W-CDMA
- Private Land Mobile Radio

#### **Functional Diagram**



#### Features

Noise Figure: 0.9 dB Output IP3: +35 dBm Gain: 14 dB Low Loss LNA Bypass Path Single Supply: +5V @ 90 mA 50 Ohm Matched Output

#### **General Description**

The HMC373LP3 / HMC373LP3E are versatile, high dynamic range GaAs MMIC Low Noise Amplifiers that integrates a low loss LNA bypass mode on the IC. The amplifier is ideal for GSM & CDMA cellular basestation front-end receivers operating between 700 and 1000 MHz and provides 0.9 dB noise figure, 14 dB of gain and +35 dBm IP3 from a single supply of +5V @ 90 mA. Input and output return losses are 28 and 12 dB respectively with the LNA requiring minimal external components to optimize the RF input match, RF ground and DC bias. By presenting an open or short circuit to a single control line, the LNA can be switched into a low 2.0 dB loss bypass mode reducing the current consumption to 10 µA. For applications which require improved noise figure, please see the HMC668LP3(E).

Devemeter		LNA Mode		LNA Mode			Bypass Mode			Linita
Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		810 - 960	)	7	700 - 100	0	7	700 - 100	0	MHz
Gain	11.5	13.5		10.5	14		-2.8	-2.0		dB
Gain Variation Over Temperature		0.008	0.015		0.008	0.015		0.002	0.004	dB / °C
Noise Figure		0.9	1.3		1.0	1.4				dB
Input Return Loss		28			25			30		dB
Output Return Loss		12			11			25		dB
Reverse Isolation		20			19					dB
Power for 1dB Compression (P1dB)*	18	21		17	20			30		dBm
Saturated Output Power (Psat)		22.5			22					dBm
Third Order Intercept (IP3)* (-20 dBm Input Power per tone, 1 MHz tone spacing)		35.5			35			50		dBm
Supply Current (Idd)		90			90			0.01		mA

#### Electrical Specifications, $T_{A} = +25^{\circ}$ C, Vdd = +5V

\* P1dB and IP3 for LNA Mode are referenced to RFOUT while P1dB and IP3 for Bypass Mode are referenced to RFIN.

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third paties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.





# GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz



LNA Gain vs. Temperature



LNA Gain vs. Vdd



LNA – Gain, Noise Figure & Power vs. Supply Voltage @ 850 MHz



LNA Noise Figure vs. Temperature



LNA Noise Figure vs. Vdd



Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.





GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz

#### LNA Input Return Loss vs. Temperature -5 -10 (dB) +25 C +85 C -40 C ٦. -15 RETURN LOSS -20 -25 -30 -35 -40 0.75 0.85 0.9 0.95 0.7 0.8 1 FREQUENCY (GHz)

v03.0610

LNA Output IP3 vs. Temperature



LNA Output IP3 vs. Vdd



#### LNA Output Return Loss vs. Temperature



#### LNA P1dB & Psat vs. Temperature



#### LNA P1dB vs. Vdd



Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.





#### v03.0610 GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz

#### LNA Reverse Isolation vs. Temperature



Bypass Mode Insertion Loss vs. Temperature



Bypass Mode Output Return Loss vs. Temperature



Bypass Mode Broadband Insertion Loss & Return Loss



Bypass Mode Input Return Loss vs. Temperature



Bypass Mode Input IP3 vs. Temperature



Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.



Idd (mA)

87

90

93

Vctl= Short Circuit to DC Ground Vctl= Open Circuit



GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz

Vdd (Vdc)

+4.5

+5.0

+5.5

LNA Mode

**Bypass Mode** 

**Truth Table** 

Typical Supply Current vs. Vdd

#### Absolute Maximum Ratings

+8.0 Vdc		
+15 dBm +30 dBm		
150 °C		
0.878 W		
74.1 °C/W		
-65 to +150° C		
-40 to +85° C		



#### ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

### **Outline Drawing**







#### NOTES:

1. LEADFRAME MATERIAL: COPPER ALLOY

- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM.
- PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN

#### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking <sup>[3]</sup>
HMC373LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 <sup>[1]</sup>	373 XXXX
HMC373LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[2]</sup>	<u>373</u> XXXX

[1] Max peak reflow temperature of 235  $^\circ\text{C}$ 

[2] Max peak reflow temperature of 260  $^\circ\text{C}$ 

[3] 4-Digit lot number XXXX

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.



v03.0610



### GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz

### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 3, 5, 8, 10, 12, 13, 15, 16	N/C	No connection necessary. These pins may be connected to RF/DC ground.	
2	RFIN	This pin is matched to 50 Ohms with a 19 nH inductor to ground. See Application Circuit.	RFIN O
4	Vctl	DC ground return. LNA is in high gain mode when a short circuit is introduced to this pin through an external switch. LNA is in bypass mode when open circuit is introduced	ACG O Vetl
6	ACG	An external capacitor of 0.01μF to ground is required for low frequency bypassing. See Application Circuit for further details.	ACG Vdd
7, 14	GND	These pins must be connected to RF/DC ground.	
9	Vdd	Power supply voltage. Choke inductor and bypass capacitor are required. See application circuit.	
11	RFOUT	This pin is AC coupled and matched to 50 Ohms.	

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.



v03.0610



### GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz

#### **Evaluation PCB**



#### List of Materials for Evaluation PCB 107220 [1]

Item	Description
J1 - J2	PCB Mount SMA RF Connector
J3 - J4	DC Pin
J5	2 Pos DIP Switch
C1	10000 pF Capacitor, 0402 Pkg.
C2	10000 pF Capacitor, 0603 Pkg.
C3	1000 pF Capacitor, 0402 Pkg.
L1	19 nH Inductor, 0402 Pkg.
L2	18 nH Inductor, 0603 Pkg.
R1	2 Ohm Resistor, 0402 Pkg.
U1	HMC373LP3 / HMC373LP3E Amplifier
PCB [2]	107177 Evaluation Board

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.



v03.0610



### GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 700 - 1000 MHz

### **Evaluation Board Circuit**



#### **Application Circuit**



Note 1: Choose value of capacitor C1 for low frequency bypassing. A 0.01  $\mu$ F ±10% capacitor is recommended.

Note 2: Pin 4 (Vctl) is the DC ground return for the circuit. The LNA is in the high gain mode when a short circuit is introduced to this pin through an external switch. The LNA is in bypass mode when an open circuit is introduced. For the data presented, switching is done through a two position DIP switch (J5) in series with a 2 Ohm resistor (to account for the Ron of an electrical switch).

Note 3: L1, L2 and C1 should be located as close to pins as possible.

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Amplifier category:

Click to view products by Analog Devices manufacturer:

Other Similar products are found below :

ADPA7006AEHZ CXE2089ZSR MGA-43828-BLKG A82-1 RF2878TR7 BGA 728L7 E6327 BGB719N7ESDE6327XTMA1 HMC1126-SX HMC342 HMC561-SX HMC598-SX HMC-ALH382-SX HMC-ALH476-SX SE2433T-R SE2622L-R SMA3101-TL-E SMA39 SMA70-1 A66-1 A66-3 A67-1 LX5535LQ LX5540LL RF2373TR7 HMC3653LP3BETR HMC395 HMC549MS8GETR HMC576-SX HMC754S8GETR HMC-ALH435-SX SMA101 SMA1031 SMA181 SMA32 SMA411 SMA531 SST12LP17E-XX8E SST12LP19E-QX6E TGA2598 WPM0510A HMC5929LS6TR HMC5879LS7TR HMC906A-SX HMC1127 HMC544A HMC1126 HMC1110-SX HMC1087F10 HMC1086 HMC1016